COMPLEMENTARY SILICON POWER TRANSISTORS

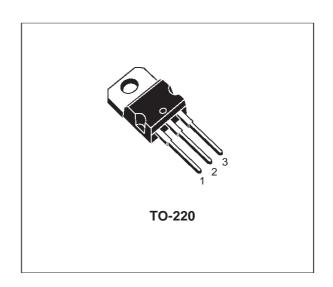
 STMicroelectronics PREFERRED SALESTYPES

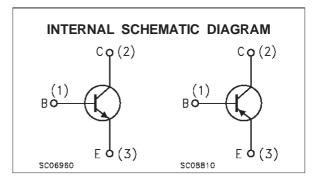
DESCRIPTION

The BD243B and BD243C are silicon Epitaxial-Base NPN transistors mounted in Jedec TO-220 plastic package.

They are inteded for use in medium power linear and switching applications.

The complementary PNP types are BD244B and BD244C respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Va	Unit		
		NPN	BD243B	BD243C	
		PNP	BD244B	BD244C	
V_{CBO}	Collector-Base Voltage (I _E = 0)	80	100	V	
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	80	100	V	
V_{EBO}	Emitter-Base Voltage (I _C = 0)	5		V	
Ic	Collector Current	6		А	
I_{CM}	Collector Peak Current	10		А	
lΒ	Base Current	2		А	
P_{tot}	Total Dissipation at T _c ≤ 25 °C	65		W	
T_{stg}	Storage Temperature	-65 to	°C		
Tj	Max. Operating Junction Temperature	15	°C		

For PNP types voltage and current values are negative.

September 1999

BD243B / BD243C / BD244B / BD244C

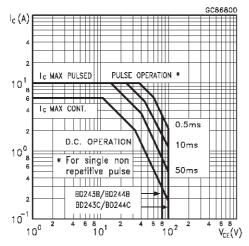
THERMAL DATA

R _{thj-case}	Thermal Res	sistance	Junction-case	Max	1.92	°C/W
R _{thj-amb}	Thermal Res	sistance	Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ °C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = rated V	/сео			0.4	mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 60 V				0.7	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 30 mA for BD243B/E for BD243C/E		80 100			> >
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 6 A	I _B = 1 A			1.5	V
V _{BE} *	Base-Emitter Voltage	I _C = 6 A	$V_{CE} = 4 V$			2	V
h _{FE} *	DC Current Gain	I _C = 0.3 A I _C = 3 A	V _{CE} = 4 V V _{CE} = 4 V	30 15			
h _{fe}	Small Signal Current Gain	_	$V_{CE} = 10 \text{ V}$ f = 1MHz $V_{CE} = 10 \text{ V}$ f = 1KHz	3 20			

Safe Operating Area

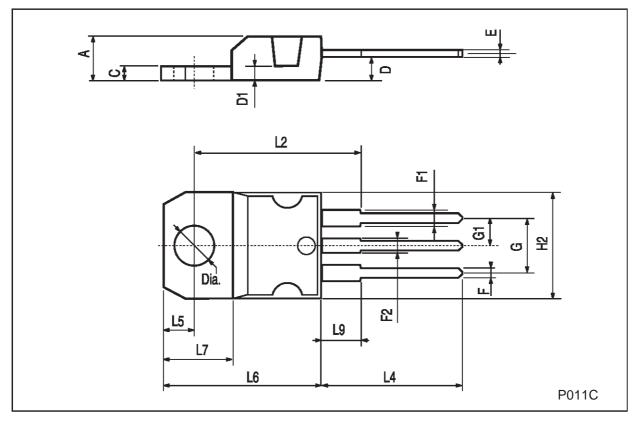


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^{*} Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 % For PNP types voltage and current values are negative.

TO-220 MECHANICAL DATA

DIM.		mm			inch	
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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